Izabella Grzegory

List of Publications by Year
in descending order

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441 papers	12,743 citations	31976 53 h-index	36028 97 g-index
443 all docs	443 docs citations	443 times ranked	5887 citing authors

#	Article	IF	Citations
1	Elastic constants of gallium nitride. Journal of Applied Physics, 1996, 79, 3343-3344.	2.5	642
2	Raman scattering and x-ray-absorption spectroscopy in gallium nitride under high pressure. Physical Review B, 1992, 45, 83-89.	3.2	544
3	Observation of Native Ga Vacancies in GaN by Positron Annihilation. Physical Review Letters, 1997, 79, 3030-3033.	7.8	459
4	Lattice parameters of gallium nitride. Applied Physics Letters, 1996, 69, 73-75.	3.3	373
5	Towards the Identification of the Dominant Donor in GaN. Physical Review Letters, 1995, 75, 296-299.	7.8	295
6	Photoluminescence and reflectance spectroscopy of excitonic transitions in high-quality homoepitaxial GaN films. Physical Review B, 1999, 60, 1471-1473.	3.2	220
7	Thermal expansion of gallium nitride. Journal of Applied Physics, 1994, 76, 4909-4911.	2.5	211
8	Mechanism of yellow luminescence in GaN. Applied Physics Letters, 1995, 67, 2188-2190.	3.3	208
9	Investigation of longitudinalâ€optical phononâ€plasmon coupled modes in highly conducting bulk GaN. Applied Physics Letters, 1995, 67, 2524-2526.	3.3	207
10	Elastic and plastic properties of GaN determined by nano-indentation of bulk crystal. Applied Physics Letters, 1999, 75, 2070-2072.	3.3	204
11	Hardness and fracture toughness of bulk single crystal gallium nitride. Applied Physics Letters, 1996, 69, 4044-4046.	3.3	182
12	Phonon Dispersion Curves in Wurtzite-Structure GaN Determined by Inelastic X-Ray Scattering. Physical Review Letters, 2001, 86, 906-909.	7.8	176
13	Temperature dependence of the energy gap in GaN bulk single crystals and epitaxial layer. Journal of Applied Physics, 1994, 76, 2429-2434.	2.5	171
14	Thermodynamical properties of IIIâ€“V nitrides and crystal growth of GaN at high N2 pressure. Journal of Crystal Growth, 1997, 178, 174-188.	1.5	169
15	Chemical polishing of bulk and epitaxial GaN. Journal of Crystal Growth, 1997, 182, 17-22.	1.5	161
16	Pressure studies of gallium nitride: Crystal growth and fundamental electronic properties. Physical Review B, 1992, 45, 13307-13313.	3.2	152
17	Thermal conductivity of GaN crystals in 4.2â€300 K range. Solid State Communications, 2003, 128, 69-73.	1.9	152
18	Exciton region reflectance of homoepitaxial GaN layers. Applied Physics Letters, 1996, 69, 788-790.	3.3	141

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19	Determination of the effective mass of GaN from infrared reflectivity and Hall effect. Applied Physics Letters, 1996, 68, 1114-1116.	3.3	137
20	IIIâ€“V Nitridesâ€”thermodynamics and crystal growth at high N2 pressure. Journal of Physics and Chemistry of Solids, 1995, 56, 639-647.	4.0	130
21	Luminescence and reflectivity in the exciton region of homoepitaxial GaN layers grown on GaN substrates. Solid State Communications, 1996, 97, 919-922.	1.9	130
22	Thermal stability of isolated and complexed Ga vacancies in GaN bulk crystals. Physical Review B, 2001, 64, .	3.2	129
23	High electron mobility in AlGaN/GaN heterostructures grown on bulk GaN substrates. Applied Physics Letters, 2000, 77, 2551-2553.	3.3	119
24	Recent advances in defect-selective etching of GaN. Journal of Crystal Growth, 2000, 210, 151-156.	1.5	117
25	Orthodox etching of HVPE-grown GaN. Journal of Crystal Growth, 2007, 305, 384-392.	1.5	113
26	Thermal properties of indium nitride. Journal of Physics and Chemistry of Solids, 1998, 59, 289-295.	4.0	110
27	Homoepitaxy of GaN on polished bulk single crystals by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 68, 917-919.	3.3	107
28	Influence of dopants and substrate material on the formation of Ga vacancies in epitaxial GaN layers. Physical Review B, 2001, 63, .	3.2	104
29	Negative differential resistance in dislocation-free GaNâ•AlGaN double-barrier diodes grown on bulk GaN. Applied Physics Letters, 2006, 88, 172106.	3.3	99
30	Effect of growth polarity on vacancy defect and impurity incorporation in dislocation-free GaN. Applied Physics Letters, 2005, 86, 031915.	3.3	96
31	Defect-selective etching of GaN in a modified molten bases system. Journal of Crystal Growth, 2002, 246, 21-24.	1.5	93
32	Polariton effects in reflectance and emission spectra of homoepitaxial GaN. Physical Review B, 1997, 56, 15151-15156.	3.2	90
33	GaNâ€“AlGaN heterostructure field-effect transistors over bulk GaN substrates. Applied Physics Letters, 2000, 76, 3807-3809.	3.3	90
34	Mg-doped GaN: Similar defects in bulk crystals and layers grown on Al2O3 by metalâ€“organic chemical-vapor deposition. Applied Physics Letters, 1999, 75, 4159-4161.	3.3	86
35	Structural characterization of bulk GaN crystals grown under high hydrostatic pressure. Journal of Electronic Materials, 1996, 25, 1545-1550.	2.2	85
36	Morphological and structural characteristics of homoepitaxial GaN grown by metalorganic chemical vapour deposition (MOCVD). Journal of Crystal Growth, 1999, 204, 419-428.	1.5	84

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37	Optical and magnetic properties of Mn in bulk GaN. Physical Review B, 2004, 69, .	3.2	84
38	High pressure growth of bulk GaN from solutions in gallium. Journal of Physics Condensed Matter, 2001, 13, 6875-6892.	1.8	82
39	Carrier recombination at single dislocations in GaN measured by cathodoluminescence in a transmission electron microscope. Journal of Applied Physics, 2002, 92, 2000-2005.	2.5	82
40	The influence of Mg doping on the formation of Ga vacancies and negative ions in GaN bulk crystals. Applied Physics Letters, 1999, 75, 2441-2443.	3.3	77
41	Carrier localization of as-grownn-type gallium nitride under large hydrostatic pressure. Physical Review B, 1996, 53, 1322-1326.	3.2	76
42	Degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. Applied Physics Letters, 2006, 88, 201111.	3.3	75
43	Nonradiative recombination at threading dislocations in n-type GaN: Studied by cathodoluminescence and defect selective etching. Applied Physics Letters, 2008, 92, .	3.3	74
44	Structure and composition of GaN(0001) A and B surfaces. Journal of Applied Physics, 1999, 85, 7697-7704.	2.5	69
45	Heat capacity ofÎ±â^'GaN: Isotope effects. Physical Review B, 2005, 72, .	3.2	68
46	Deposition of thick GaN layers by HVPE on the pressure grown GaN substrates. Journal of Crystal Growth, 2005, 281, 38-46.	1.5	66
47	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 011114.	3.3	66
48	High pressure phase transition in aluminium nitride. Solid State Communications, 1991, 79, 1033-1034.	1.9	65
49	Lattice constants, thermal expansion and compressibility of gallium nitride. Journal Physics D: Applied Physics, 1995, 28, A149-A153.	2.8	65
50	Homo-epitaxial GaN growth on exact and misoriented single crystals: suppression of hillock formation. Journal of Crystal Growth, 2000, 210, 435-443.	1.5	62
51	Spontaneous Ordering in Bulk GaN:Mg Samples. Physical Review Letters, 1999, 83, 2370-2373.	7.8	56
52	Mechanisms of crystallization of bulk GaN from the solution under high N2 pressure. Journal of Crystal Growth, 2002, 246, 177-186.	1.5	54
53	Neutral Mn acceptor in bulk GaN in high magnetic fields. Physical Review B, 2004, 70, .	3.2	54
54	Chemically orderedAlxGa1â^'xNalloys:â€ƒSpontaneous formation of natural quantum wells. Physical Review B, 2005, 71, .	3.2	53

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55	The microstructure of gallium nitride monocrystals grown at high pressure. Journal of Crystal Growth, 1996, 169, 235-242.	1.5	51
56	Acoustic phonon scattering of two-dimensional electrons in GaN/AlGaN heterostructures. Applied Physics Letters, 2002, 80, 1228-1230.	3.3	51
57	Preparation of Free-Standing GaN Substrates from Thick GaN Layers Crystallized by Hydride Vapor Phase Epitaxy on Ammonothermally Grown GaN Seeds. Applied Physics Express, 2013, 6, 075504.	2.4	51
58	Raman and cathodoluminescence study of dislocations in GaN. Journal of Applied Physics, 2002, 92, 6666-6670.	2.5	49
59	High-Resolution Photoluminescence and Reflectance Spectra of Homoepitaxial GaN Layers. Physica Status Solidi (B): Basic Research, 1999, 216, 5-9.	1.5	48
60	60mW continuous-wave operation of InGaN laser diodes made by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2006, 88, 221108.	3.3	48
61	X-ray examination of GaN single crystals grown at high hydrostatic pressure. Journal of Crystal Growth, 1993, 126, 601-604.	1.5	46
62	High Quality Homoepitaxial GaN Grown by Molecular Beam Epitaxy with NH 3 on Surface Cracking. Japanese Journal of Applied Physics, 1997, 36, L1634-L1636.	1.5	46
63	Symmetry of excitons in GaN. Physical Review B, 1999, 60, 4438-4441.	3.2	45
64	Nitride-based laser diodes by plasma-assisted MBEâ€"From violet to green emission. Journal of Crystal Growth, 2009, 311, 1632-1639.	1.5	45
65	GaN substrates for molecular beam epitaxy growth of homoepitaxial structures. Thin Solid Films, 2000, 367, 281-289.	1.8	44
66	Temperature dependence of electrical properties of gallium-nitride bulk single crystals doped with Mg and their evolution with annealing. Journal of Applied Physics, 2001, 89, 7960-7965.	2.5	44
67	HVPE-GaN grown on MOCVD-GaN/sapphire template and ammonothermal GaN seeds: Comparison of structural, optical, and electrical properties. Journal of Crystal Growth, 2014, 394, 55-60.	1.5	44
68	Crystal growth of III-N compounds under high nitrogen pressure. Physica B: Condensed Matter, 1993, 185, 99-102.	2.7	43
69	Homoepitaxial growth of GaN by metalorganic vapor phase epitaxy: A benchmark for GaN technology. Applied Physics Letters, 1999, 75, 1098-1100.	3.3	43
70	Decay of stimulated and spontaneous emission in highly excited homoepitaxial GaN. Applied Physics Letters, 2001, 78, 3776-3778.	3.3	43
71	Dry etching of GaN substrates for high-quality homoepitaxy. Applied Physics Letters, 1999, 74, 1123-1125.	3.3	42
72	Optical properties of GaN epilayers and GaN/AlGaN quantum wells grown by molecular beam epitaxy on GaN(0001) single crystal substrate. Journal of Applied Physics, 2000, 88, 183-187.	2.5	42

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73	Ordering in bulk GaN:Mg samples: defects caused by Mg doping. Physica B: Condensed Matter, 1999, 273-274, 124-129.	2.7	41
74	Fully-screened polarization-induced electric fields in blueâˆ•violet InGaNâˆ•GaN light-emitting devices grown on bulk GaN. Applied Physics Letters, 2005, 87, 041109.	3.3	41
75	Structural Defects in Heteroepitaxial and Homoepitaxial GaN. Materials Research Society Symposia Proceedings, 1995, 395, 351.	0.1	40
76	X-ray absorption, glancing-angle reflectivity, and theoretical study of the N K- and GaM2,3-edge spectra in GaN. Physical Review B, 1997, 55, 2612-2622.	3.2	40
77	Crystal growth of aluminum nitride under high pressure of nitrogen. Materials Science in Semiconductor Processing, 2001, 4, 543-548.	4.0	39
78	Surface reaction of nitrogen with liquid group III metals. Journal of Chemical Physics, 2001, 114, 6353-6363.	3.0	39
79	The influence of lattice parameter variation on microstructure of GaN single crystals. Journal of Alloys and Compounds, 2005, 401, 261-264.	5.5	37
80	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. Applied Physics Letters, 2007, 91, .	3.3	37
81	GaN homoepitaxial layers grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1999, 75, 1276-1278.	3.3	36
82	GaN/AlGaN quantum wells for UV emission: heteroepitaxy versus homoepitaxy. Semiconductor Science and Technology, 2001, 16, 358-361.	2.0	36
83	Growth optimisation of the GaN layers and GaN/AlGaN heterojunctions on bulk GaN substrates using plasma-assisted molecular beam epitaxy. Physica Status Solidi A, 2004, 201, 320-323.	1.7	36
84	High power blueâ€“violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. Semiconductor Science and Technology, 2005, 20, 809-813.	2.0	36
85	Application of a composite plasmonic substrate for the suppression of an electromagnetic mode leakage in InGaN laser diodes. Applied Physics Letters, 2009, 95, .	3.3	36
86	Homoepitaxial growth of GaN using molecular beam epitaxy. Journal of Applied Physics, 1996, 80, 2195-2198.	2.5	35
87	Different character of the donor-acceptor pair-related 3.27 eV band and blue photoluminescence in Mg-doped GaN. Hydrostatic pressure studies. Physical Review B, 2000, 62, 10151-10157.	3.2	35
88	Annealing of GaN under high pressure of nitrogen. Journal of Physics Condensed Matter, 2002, 14, 11097-11110.	1.8	35
89	Thermal conductivity of GaN crystals grown by high pressure method. Physica Status Solidi (B): Basic Research, 2003, 240, 447-450.	1.5	35
90	Magnetic anisotropy of bulk GaN:Mn single crystals codoped with Mg acceptors. Physical Review B, 2005, 71, .	3.2	35

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91	Growth of InGaN and InGaN/InGaN quantum wells by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 3983-3986.	1.5	35
92	GaN crystallization by the high-pressure solution growth method on HVPE bulk seed. Journal of Crystal Growth, 2008, 310, 3924-3933.	1.5	35
93	Molecular doping of gallium nitride. Applied Physics Letters, 1999, 74, 416-418.	3.3	34
94	Properties of metal-insulator transition and electron spin relaxation in GaN:Si. Physical Review B, 2011, 83, .	3.2	34
95	The challenge of decomposition and melting of gallium nitride under high pressure and high temperature. Journal of Physics and Chemistry of Solids, 2015, 85, 138-143.	4.0	34
96	Interaction of N2 molecule with liquid Ga surface â€“ quantum mechanical calculations (DFT). Journal of Crystal Growth, 1998, 189-190, 159-162.	1.5	33
97	Optically detected magnetic resonance of the red and near-infrared luminescence in Mg-doped GaN. Physical Review B, 2001, 63, .	3.2	32
98	Directional crystallization of GaN on high-pressure solution grown substrates by growth from solution and HVPE. Journal of Crystal Growth, 2002, 246, 194-206.	1.5	32
99	InGaN light emitting diodes for 415 nmâ€“520 nm spectral range by plasma assisted MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S917.	0.8	32
100	Evidence of free carrier concentration gradient along the c-axis for undoped GaN single crystals. Journal of Crystal Growth, 2001, 230, 442-447.	1.5	31
101	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, 172117.	3.3	31
102	Multi feed seed (MFS) high pressure crystallization of 1â€“2in GaN. Journal of Crystal Growth, 2012, 350, 5-10.	1.5	31
103	Homoepitaxial HVPE-GaN growth on non-polar and semi-polar seeds. Journal of Crystal Growth, 2014, 403, 48-54.	1.5	31
104	A pressure-tuned blue-violet InGaN/GaN laser diode grown on bulk GaN crystal. Applied Physics Letters, 2004, 84, 1236-1238.	3.3	30
105	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. Applied Physics Letters, 2006, 88, 141909.	3.3	30
106	High Resistivity GaN Single Crystalline Substrates. Acta Physica Polonica A, 1997, 92, 958-962.	0.5	30
107	Transverse effective charge and its pressure dependence in GaN single crystals. Physical Review B, 1999, 60, 1480-1483.	3.2	29
108	High-nitrogen-pressure growth of GaN single crystals: doping and physical properties. Journal of Physics Condensed Matter, 2001, 13, 8881-8890.	1.8	29

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109	Free and bound excitons in GaNâˆ•AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112Â¯0) direction. Applied Physics Letters, 2005, 86, 162112.	3.3	29
110	Growth of thin AlInNâˆ•GaInN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. Journal of Vacuum Science & Technology B, 2006, 24, 1505.	1.3	29
111	Crystallization of low dislocation density GaN by high-pressure solution and HVPE methods. Journal of Crystal Growth, 2007, 300, 17-25.	1.5	29
112	Homoepitaxial growth of HVPE-GaN doped with Si. Journal of Crystal Growth, 2016, 456, 91-96.	1.5	29
113	Ga vacancies in electron irradiated GaN: introduction, stability and temperature dependence of positron trapping. Physica B: Condensed Matter, 2001, 308-310, 77-80.	2.7	28
114	Structural and Optical Properties of Homoepitaxial GaN Layers. Materials Research Society Symposia Proceedings, 1996, 449, 393.	0.1	27
115	Selective excitation and thermal quenching of the yellow luminescence of GaN. Applied Physics Letters, 1999, 75, 3273-3275.	3.3	27
116	High-pressure crystallization of GaN for electronic applications. Journal of Physics Condensed Matter, 2002, 14, 11055-11067.	1.8	27
117	Characterization of GaN single crystals by defect-selective etching. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 821-826.	0.8	27
118	Intrinsic dynamics of weakly and strongly confined excitons in nonpolar nitride-based heterostructures. Physical Review B, 2011, 83, .	3.2	27
119	Defects in GaN single crystals and homoepitaxial structures. Journal of Crystal Growth, 2005, 281, 135-142.	1.5	26
120	Examination of defects and the seed's critical thickness in HVPEâ€GaN growth on ammonothermal GaN seed. Physica Status Solidi (B): Basic Research, 2015, 252, 1172-1179.	1.5	26
121	Vacancies as compensating centers in bulk GaN: doping effects. Journal of Crystal Growth, 2002, 246, 281-286.	1.5	25
122	Fine Structure of Effective Mass Acceptors in Gallium Nitride. Physical Review Letters, 2003, 91, 226404.	7.8	25
123	Deposition of bulk GaN from solution in gallium under high N2 pressure on silicon carbide and sapphire substrates. Journal of Crystal Growth, 2004, 270, 409-419.	1.5	25
124	Revealing extended defects in HVPE-grown GaN. Journal of Crystal Growth, 2010, 312, 2611-2615.	1.5	25
125	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C136.	1.2	25
126	GaN Crystals: Growth and Doping Under Pressure. Materials Research Society Symposia Proceedings, 1997, 482, 115.	0.1	24

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127	Analysis of self-lift-off process during HVPE growth of GaN on MOCVD-GaN/sapphire substrates with photolitographically patterned Ti mask. Journal of Crystal Growth, 2013, 380, 99-105.	1.5	24
128	Recent Results in the Crystal Growth of GaN at High N₂ Pressure. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	23
129	Photoluminescence study on GaN homoepitaxial layers grown by molecular beam epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	23
130	Observation of Ga vacancies and negative ions in undoped and Mg-doped GaN bulk crystals. Physica B: Condensed Matter, 1999, 273-274, 33-38.	2.7	23
131	Spin and interaction effects in Shubnikovâ€“de Haas oscillations and the quantum Hall effect in GaN/AlGaN heterostructures. Journal of Physics Condensed Matter, 2004, 16, 3421-3432.	1.8	23
132	CFD and reaction computational analysis of the growth of GaN by HVPE method. Journal of Crystal Growth, 2006, 296, 31-42.	1.5	23
133	GaN doped with berylliumâ€”An effective light converter for white light emitting diodes. Applied Physics Letters, 2013, 103, .	3.3	23
134	Iron and manganese as dopants used in the crystallization of highly resistive HVPE-GaN on native seeds. Japanese Journal of Applied Physics, 2019, 58, SC1047.	1.5	23
135	The Application of High Pressure in Physics and Technology of III-V Nitrides. Acta Physica Polonica A, 2001, 100, 57-109.	0.5	23
136	Effect of pressure on exciton energies of homoepitaxial GaN. Solid State Communications, 1998, 108, 433-438.	1.9	22
137	Photoemission studies on GaN(0 0 0 1) surfaces. Surface Science, 2001, 482-485, 740-745.	1.9	22
138	Polarity dependent properties of GaN layers grown by hydride vapor phase epitaxy on GaN bulk crystals. Physica Status Solidi (B): Basic Research, 2003, 240, 289-292.	1.5	22
139	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaNâ•GaN multiple quantum wells on bulk GaN substrates. Journal of Applied Physics, 2005, 97, 103507.	2.5	22
140	Anomalous temperature characteristics of single wide quantum well InGaN laser diode. Applied Physics Letters, 2006, 88, 071121.	3.3	22
141	GaN Crystals Grown in the Increased Volume High-Pressure Reactors. Materials Research Society Symposia Proceedings, 1996, 449, 35.	0.1	21
142	Energy dependence of electron inelastic mean free paths in bulk GaN crystals. Surface Science, 2004, 566-568, 1234-1239.	1.9	21
143	High pressureâ€“high temperature seeded growth of GaN on 1 in sapphire/GaN templates: Analysis of convective transport. Journal of Crystal Growth, 2007, 307, 259-267.	1.5	21
144	Preparation of free-standing GaN substrates from GaN layers crystallized by hydride vapor phase epitaxy on ammonothermal GaN seeds. Japanese Journal of Applied Physics, 2014, 53, 05FA04.	1.5	21

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145	Examination of growth rate during hydride vapor phase epitaxy of GaN on ammonothermal GaN seeds. Journal of Crystal Growth, 2014, 407, 52-57.	1.5	21
146	Spatial distribution of electron concentration and strain in bulk GaN single crystals - relation to growth mechanism. Materials Research Society Symposia Proceedings, 1996, 449, 519.	0.1	20
147	Metalâ€Insulator Transition in GaN Crystals. Physica Status Solidi (B): Basic Research, 1996, 198, 223-233.	1.5	20
148	Impurity-Related Luminescence of Homoepitaxial GaN Studied with High Magnetic Fields. Physica Status Solidi (B): Basic Research, 1998, 210, 373-383.	1.5	20
149	Selective photoluminescence spectroscopy of shallow levels in wide band gap semiconductors. Physica B: Condensed Matter, 2001, 302-303, 39-53.	2.7	20
150	Influence of Dopants on Defect Formation in GaN. Physica Status Solidi (B): Basic Research, 2001, 228, 345-352.	1.5	20
151	Stimulated emission due to spatially separated electron-hole plasma and exciton system in homoepitaxial GaN. Physical Review B, 2004, 69, .	3.2	20
152	Electronic structure of GaN(000)-(1Ã—1) surface. Surface Science, 2004, 548, 220-230.	1.9	20
153	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. Journal of Crystal Growth, 2007, 305, 346-354.	1.5	20
154	Different pressure behavior of GaN/AlGaN quantum structures grown along polar and nonpolar crystallographic directions. Journal of Applied Physics, 2009, 105, .	2.5	20
155	Growth mechanisms in semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0020.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>2</mml:mn><mml:mspace width=".5em") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 307 Td (/><mml	3.2	20
156		1.5	20
157	High-resolution PL spectra of donor- and acceptor-bound excitons in homoepitaxial GaN-layers. Physica B: Condensed Matter, 1999, 273-274, 66-69.	2.7	19
158	Growth of AlN, GaN and InN from the solution. International Journal of Materials and Product Technology, 2005, 22, 226.	0.2	19
159	Gallium nitride growth on sapphire/GaN templates at high pressure and high temperatures. Journal of Crystal Growth, 2005, 274, 55-64.	1.5	19
160	Degradation Mechanisms of InGaN Laser Diodes. Proceedings of the IEEE, 2010, 98, 1214-1219.	21.3	19
161	Ultralow threshold powers for optical pumping of homoepitaxial InGaN/GaN/AlGaN lasers. Applied Physics Letters, 2002, 81, 3735-3737.	3.3	18
162	Carrier recombination and diffusion in GaN revealed by transient luminescence under one-photon and two-photon excitations. Applied Physics Letters, 2006, 89, 172119.	3.3	18

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163	Influence of edge-grown HVPE GaN on the structural quality of c-plane oriented HVPE-GaN grown on ammonothermal GaN substrates. Journal of Crystal Growth, 2016, 456, 80-85.	1.5	18
164	Observation Of Native Ga Vacancies In Gan By Positron Annihilation. Materials Research Society Symposia Proceedings, 1997, 482, 778.	0.1	17
165	Effects of defect scattering on the photoluminescence of exciton-polaritons in n-GaN. Solid State Communications, 1998, 105, 497-501.	1.9	17
166	Energy gap in GaN bulk single crystal between 293 and 1237K. Journal of Crystal Growth, 2002, 235, 111-114.	1.5	17
167	Optical gain in homoepitaxial GaN. Applied Physics Letters, 2004, 85, 952-954.	3.3	17
168	Nitride-based quantum structures and devices on modified GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1130-1134.	1.8	17
169	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. Journal of Applied Physics, 2010, 108, 023516.	2.5	17
170	Blue Laser on High N₂Pressure-Grown Bulk GaN. Acta Physica Polonica A, 2001, 100, 229-232.	0.5	17
171	Synthesis and Crystal Growth of AIIIBVSemiconducting Compounds Under High Pressure of Nitrogen. Physica Scripta, 1991, T39, 242-249.	2.5	16
172	Blue light-emitting diodes on GaN substrates, growth and characterization. Journal of Crystal Growth, 1998, 189-190, 167-171.	1.5	16
173	Strain relaxation in AlN epitaxial layers grown on GaN single crystals. Journal of Crystal Growth, 1999, 205, 31-35.	1.5	16
174	Bulk GaN crystals grown at high pressure as substrates for blue-laser technology. Physica Status Solidi A, 2003, 200, 9-12.	1.7	16
175	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. Journal of Applied Physics, 2007, 101, 083109.	2.5	16
176	Thermal Expansion of GaN Bulk Crystals and Homoepitaxial Layers. Acta Physica Polonica A, 1996, 90, 887-890.	0.5	16
177	Photoluminescence in doped GaN bulk crystal. Journal of Physics and Chemistry of Solids, 1995, 56, 353-355.	4.0	15
178	The effect of threading dislocations, Mg doping, and etching on the spectral responsivity in GaN-based ultraviolet detectors. Journal of Applied Physics, 1999, 86, 4588-4593.	2.5	15
179	Mechanism of radiative recombination in acceptor-doped bulk GaN crystals. Physica B: Condensed Matter, 1999, 273-274, 39-42.	2.7	15
180	High pressure fabrication and processing of GaN:Mg. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 1-5.	3.5	15

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